# PUA3173 (PU3173)

## Silicon NPN triple diffusion planar type darlington

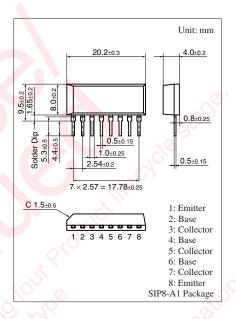
For power amplification Complementary to PUA3273 (PU3273)

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- NPN 3 elements

## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	150	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	100	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	4	A	
Peak collector current	$I_{CP}$	8	A	
Collector power dissipation	$P_{C}$	15	W	
$T_a = 25^{\circ}C$		2.4		
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 10 \text{ mA}, I_B = 0$	100	6		V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 150 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 80 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_C = 0$			5	mA
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = 4 \text{ V}, I_{C} = 2 \text{ A}$	1 000		10 000	
	h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 4 \text{ A}$	500			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 4 \text{ A}, I_B = 16 \text{ mA}$			2.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 4 \text{ A}, I_B = 16 \text{ mA}$			2.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	I <sub>C</sub> = 4 A		0.27		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 16 \text{ mA}, I_{B2} = -16 \text{ mA}$		2.9		μs
Fall time	$t_{\mathrm{f}}$	$V_{CC} = 50 \text{ V}$		1.0		μs

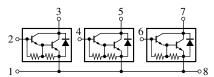
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

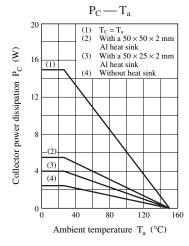
#### 2. \*: Rank classification

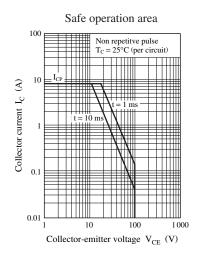
Rank	Free	Р	Q	
$h_{\mathrm{FE}}$	1000 to 10000	2000 to 10000	1000 to 5000	

Note) The part number in the parenthesis shows conventional part number.

#### ■ Internal Connection







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